

Product Summary

V_{RRM}	650 V
$I_F (T_C=150^{\circ}C)$	10 A
Q_C	31 nC

Features

- Low leakage current (I_R)
- Zero reverse recovery current
- Temperature independent switching behavior
- Positive temperature coefficient on V_F
- High surge current capacity
- Low capacitive charge

Benefits

- System cost savings due to smaller magnetics
- System efficiency improvement over Si diodes
- Reduction of heat sink requirements
- Enabling higher frequency
- Reduced EMI

Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- Server/telecom power supplies
- Power factor correction
- Solar

Package Pin Definitions

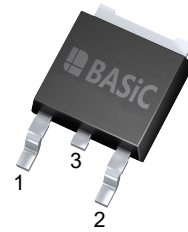
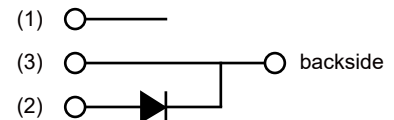
- Pin1 - NC
- Pin2 - Anode
- Pin3 and backside - Cathode

Package Parameters

Part Number	Marking	Package
B2D10065E1	B2D10065E1	TO-252-3

Packing Quantities

Tape & Reel Packing	PCS/Reel	Reels/Box	PCS/Box
TO-252-3	2500	2	5000

Package: TO-252-3

Electrical Connection


Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive peak reverse voltage		650	V
V_{RSM}	Non-repetitive peak reverse voltage		650	V
I_F	Continuous forward current	$T_c=25^\circ\text{C}$	36	A
		$T_c=135^\circ\text{C}$	16	
		$T_c=150^\circ\text{C}$	10	
I_{FSM}	Non-repetitive forward surge current	$T_c=25^\circ\text{C}$, $t_p=10\text{ms}$ Half sine wave	73	A
		$T_c=110^\circ\text{C}$, $t_p=10\text{ms}$ Half sine wave	65	
$I_{F, Max}$	Non-repetitive peak forward current	$T_c=25^\circ\text{C}$, $t_p=10\mu\text{s}$, pulse $T_c=110^\circ\text{C}$, $t_p=10\mu\text{s}$, pulse	550 520	A
$\int i^2 dt$	i^2t value	$T_c=25^\circ\text{C}$, $t_p=10\text{ms}$	26.6	A^2S
P_{tot}	Power dissipation	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	125 54	W
T_j	Operating junction temperature		-55~175	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		1.20		K/W

Electrical Characteristics
Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{DC}	DC blocking voltage	$T_J=25^{\circ}C$	650			V
V_F	Diode forward voltage	$I_F=10A$ $T_J=25^{\circ}C$ $I_F=10A$ $T_J=175^{\circ}C$		1.3 1.55	1.6 2.2	V
I_R	Reverse current	$V_R=650V$ $T_J=25^{\circ}C$ $V_R=650V$ $T_J=175^{\circ}C$		1 20	70 200	μA

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q_C	Total capacitive charge	$V_R=400V$ $T_J=25^{\circ}C$ $Q_C=\int_0^{V_R} C(V)dV$		31		nC
C	Total capacitance	$V_R=1V$ $f=1MHz$ $V_R=300V$ $f=1MHz$ $V_R=600V$ $f=1MHz$		458 54 52		pF
E_C	Capacitance stored energy	$V_R=400V$		7.7		μJ

Typical Performance

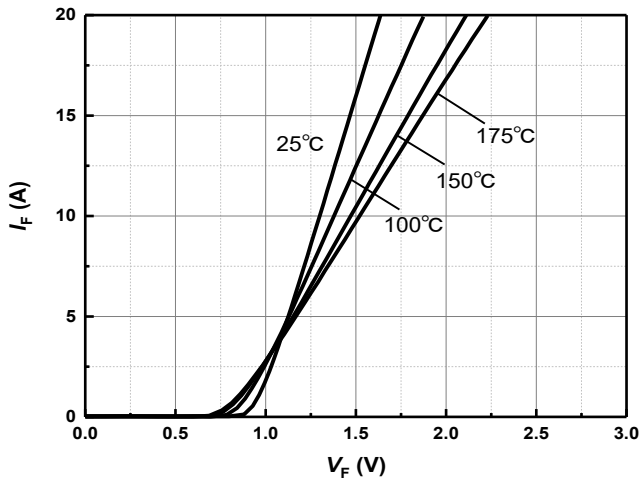


Figure 1 Typical forward characteristics

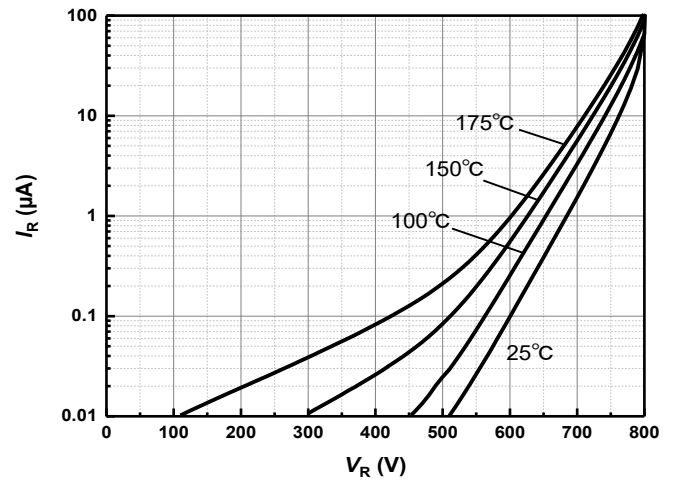


Figure 2 Typical reverse current as function of reverse voltage

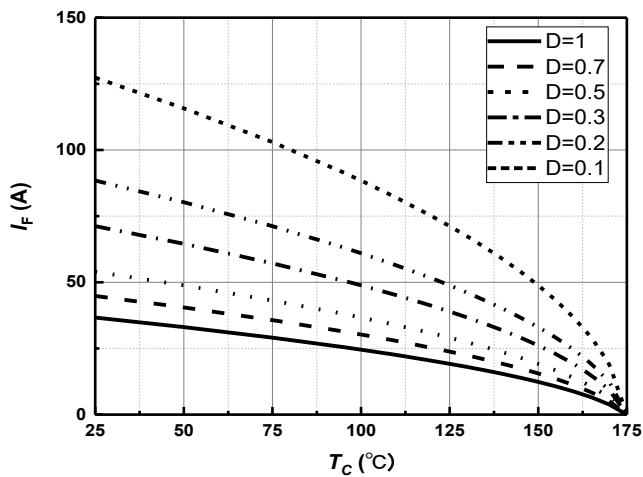


Figure 3 Diode forward current as function of temperature, D=duty cycle

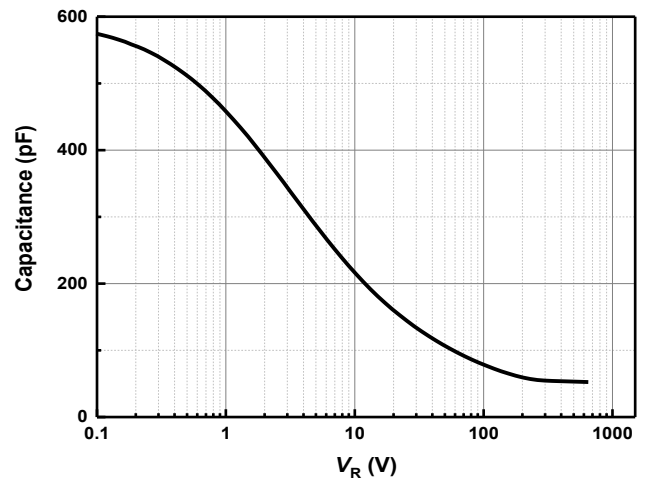


Figure 4 Typical capacitance as function of reverse voltage, $C=f(V_R)$; $T_j=25^\circ\text{C}$; $f=1\text{ MHz}$

Typical Performance

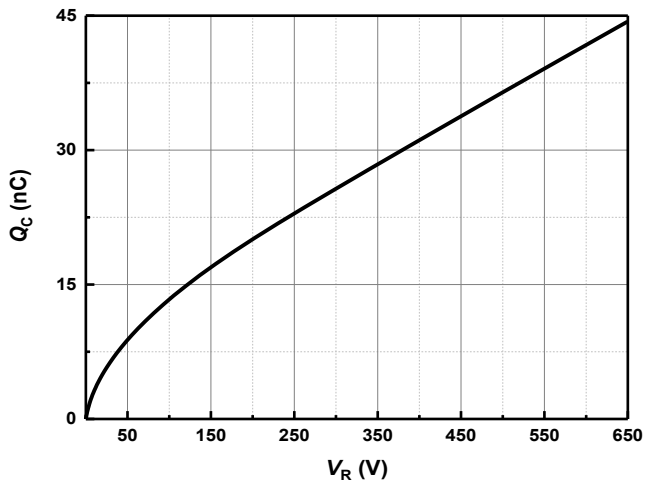


Figure 5 Typical reverse charge as function of reverse voltage

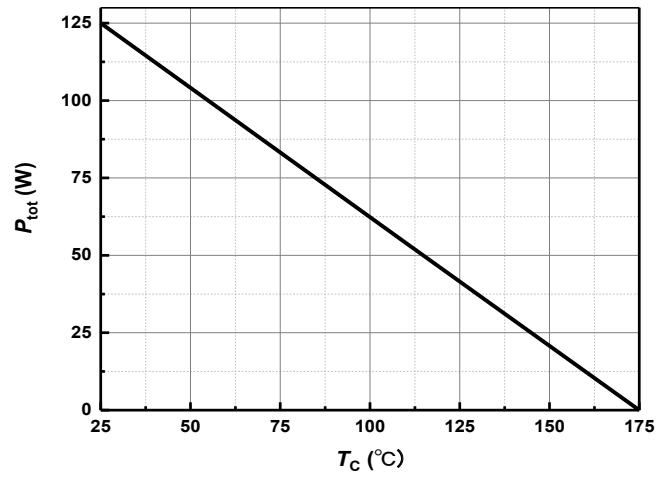


Figure 6 Power dissipation as function of case temperature

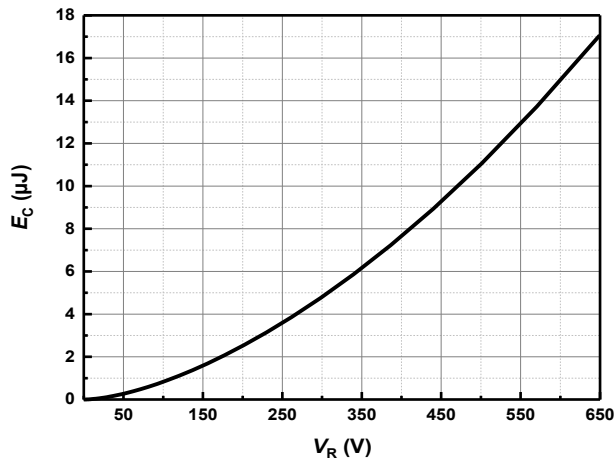


Figure 7 Capacitance stored energy

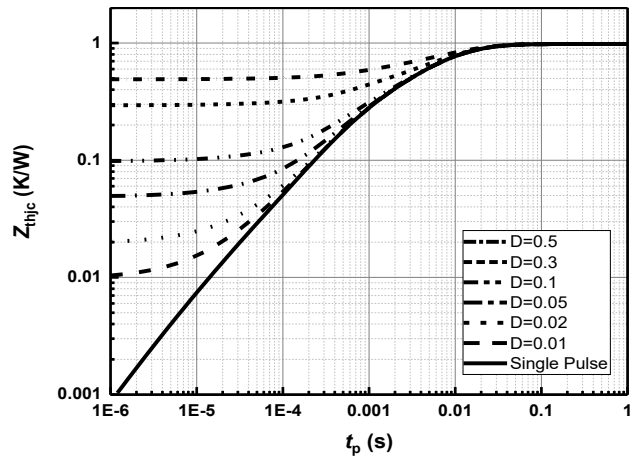


Figure 8 Max. transient thermal impedance, $Z_{thjc} = f(t)$, parameter: $D = t / T$

Typical Performance

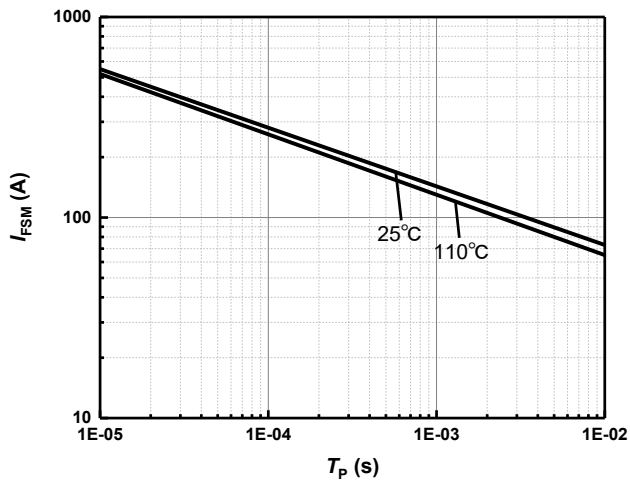
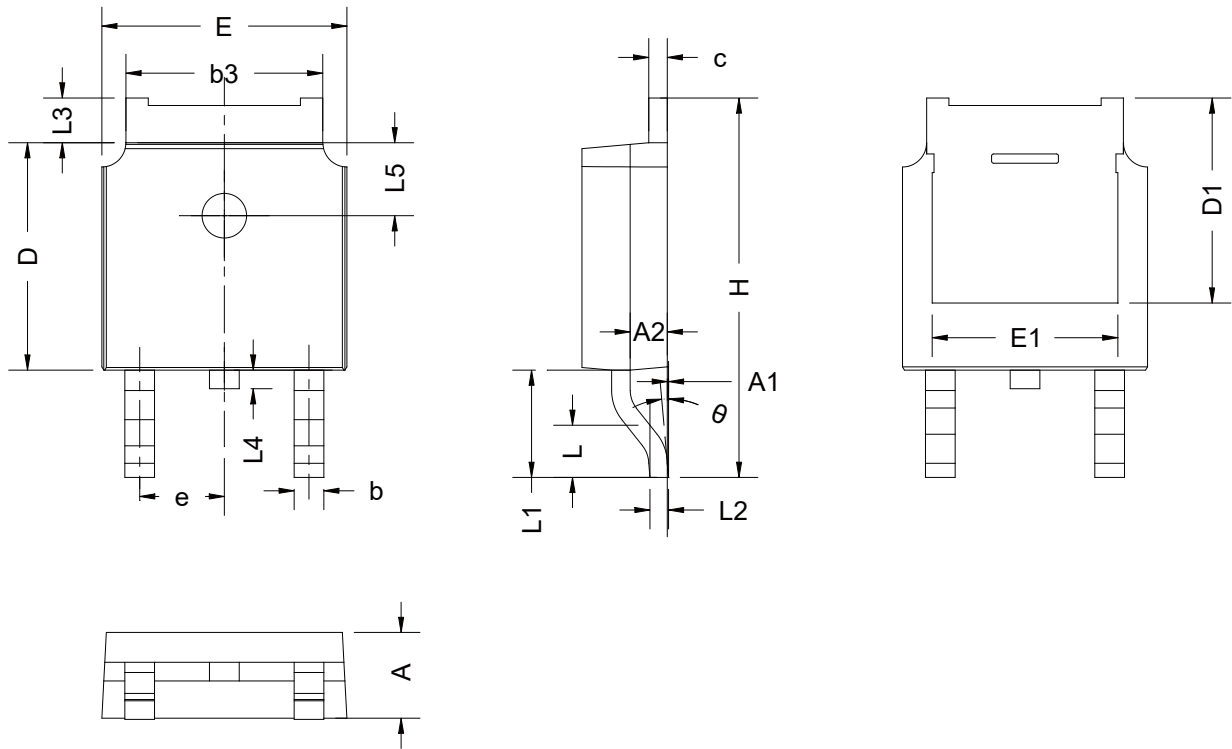
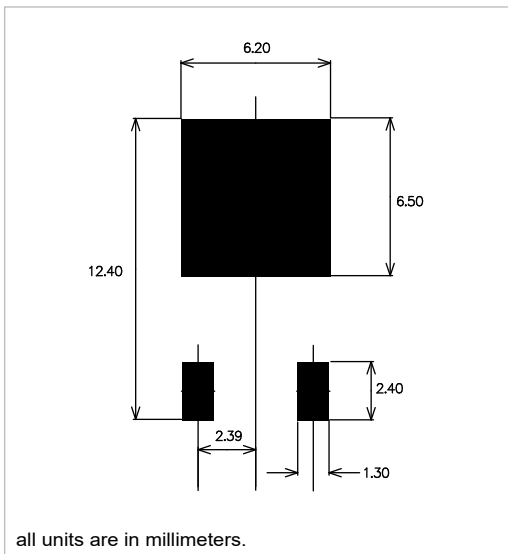


Figure 9 Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

Package Dimensions



Recommended Solder Pad Layout



SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.90	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.186	2.286	2.386
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.41	0.51	0.61
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
θ	0°	-	8°

REF: For reference only, no measurement is required.

Revision History

Document Version	Date of Release	Description of Changes
Rev. 0.0	2023-01-06	Release of the datasheet.
Rev.0.1	2023-11-30	I_{FSM} , $I_{F, Max}$, Fig9.

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